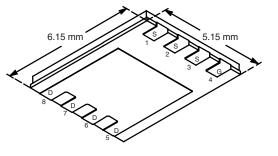


Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 20	0.0073 at V _{GS} = - 4.5 V	- 20		
	0.0090 at V_{GS} = - 2.5 V	- 18		
	0.013 at V _{GS} = - 1.8 V	- 15		





Bottom View

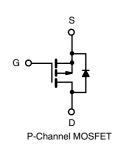
Ordering Information: Si7485DP-T1-E3 (Lead (Pb)-free) Si7485DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFETs
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile

APPLICATIONS

• Battery Switch for Portable Devices



ABSOLUTE MAXIMUM RATINGS	$T_A = 25 \ ^\circ C$, unless	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T 150 °C)a	T _A = 25 °C	– I _D	- 20	- 12.5	А
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 16.5	- 9.5	
Pulsed Drain Current		I _{DM}	- 50		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 4.5	- 1.6	
Maximum Dawar Dissinctiona	T _A = 25 °C	P _D	5	1.8	W
Maximum Power Dissipation ^a	T _A = 70 °C		3.2	1.1	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b,c}			260		C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum lumation to Ambianta	t ≤ 10 s	R _{thJA}	20	25		
Maximum Junction-to-Ambient ^a	Steady State		54	68	°C/W	
Maximum Junction-to-Case (Drain)	Steady State		1.7	2.2		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



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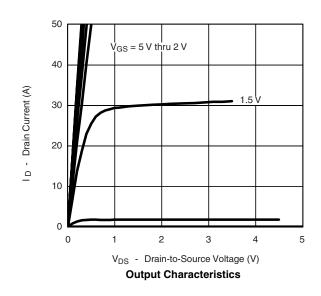
Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -1 \text{ mA}$			- 0.9	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS} –	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1		
		V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 70 °C			- 10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq$ - 5 V, V_{GS} = - 4.5 V	- 40			А	
Drain-Source On-State Resistance ^a		V_{GS} = - 4.5 V, I _D = - 20 A		0.006 0.0073			
	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -18 \text{ A}$		0.0074	0.0090	Ω	
		V _{GS} = - 1.8 V, I _D = - 15 A		0.0106	0.013		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -20 \text{ A}$		80		S	
Diode Forward Voltage ^a	V _{SD}	$I_{S} = -4.5 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.62	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Qg			99	150	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 5 V, I_D = - 20 A		11.5			
Gate-Drain Charge	Q _{gd}			29			
Gate Resistance	Rg			2.4		Ω	
Turn-On Delay Time	t _{d(on)}			80	120		
Rise Time	t_r $V_{DD} = -10 V, R_L = 10 \Omega$		140	210	1		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		360	540	ns	
Fall Time	t _f			170	260		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.9 A, dI/dt = 100 A/μs		55	80		

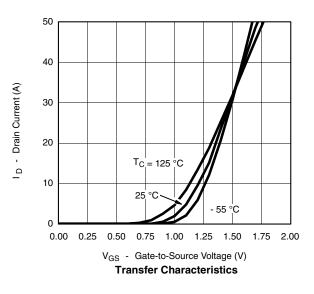
Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

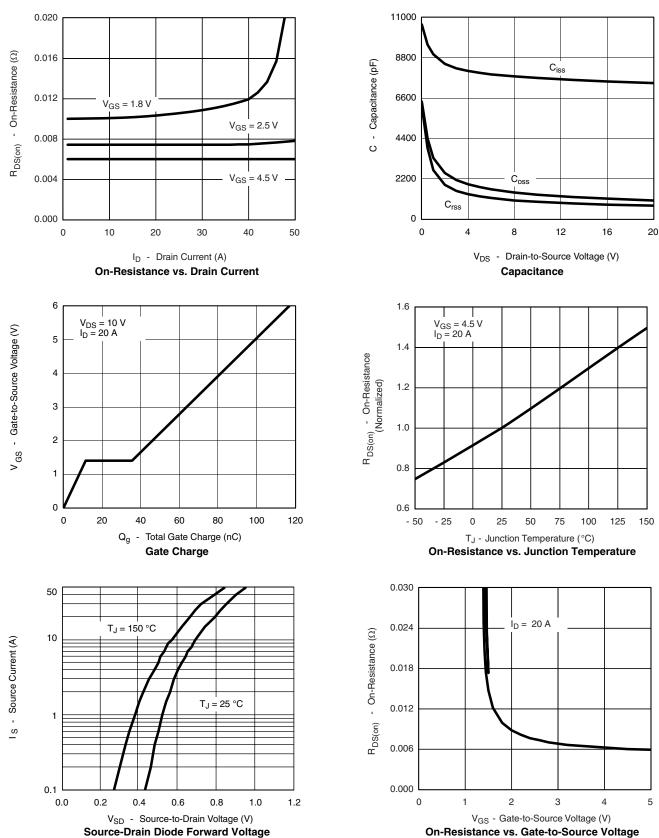




Si7485DP Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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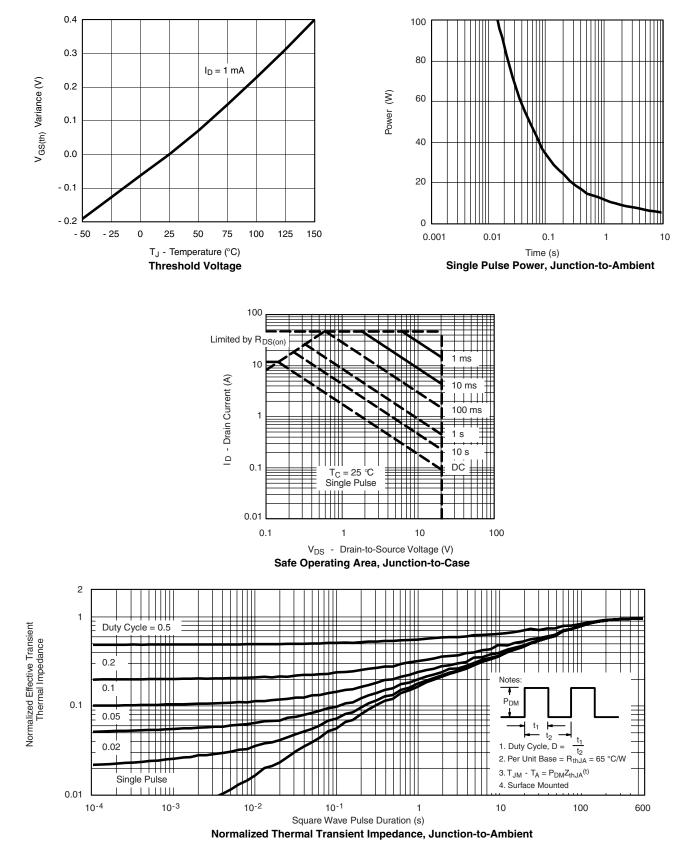
Document Number: 72275 S09-0227-Rev. C, 09-Feb-09

Si7485DP

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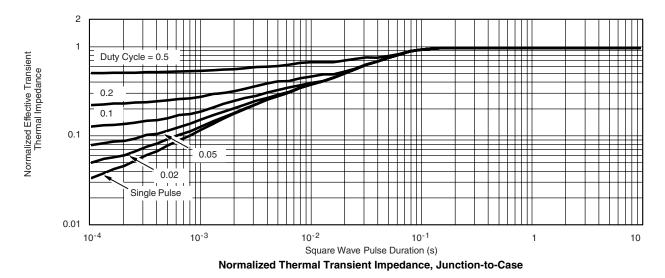
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Si7485DP Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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